

Code No: H6809/R13

M. Tech. II Semester Regular/ Supplementary Examinations, July-2016

LOW POWER VLSI DESIGN

(Common to VLSI & ES, ES & VLSI, VLSID & ES, ES & VLSID, VLSI, VLSID, VLSISD and VLSI & ME)

Time: 3 Hours

Max. Marks: 60

Answer any FIVE Questions
All Questions Carry Equal Marks

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| 1. a | Explain about switching power dissipation and short circuit power dissipation. | 8 |
| b | Briefly explain about velocity saturation. | 4 |
| 2. a | With a neat sketch, explain a variable threshold CMOS inverter circuit. | 6 |
| b | Compare pipelining and parallel processing approaches. | 6 |
| 3. a | Write down the differences between carry select adders and carry save adders. | 4 |
| b | Discuss any two types of low voltage low power logic styles. | 8 |
| 4. a | Draw the logic circuit of the conventional CMOS full adder and explain about it. | 4 |
| b | Explain the basic theory, operation and performance evaluation of carry look-ahead adders. | 8 |
| 5. a | Draw the basic building blocks of the Baugh-Wooley multiplier architecture and explain its operation. | 8 |
| b | Write down the algorithm of Baugh-Wooley multiplier. | 4 |
| 6. a | Discuss the types of multiplier architectures. | 4 |
| b | Explain about Booth multiplier. | 8 |
| 7. a | Compare SRAM and DRAM. | 4 |
| b | Give a note on future trend and development of ROM. | 4 |
| c | Write down differences between 6T and 4T static RAM cells. | 4 |
| 8. a | With a neat diagram, explain the block diagram of DRAM architecture. | 6 |
| b | Discuss low power SRAM technologies with neat diagrams. | 6 |

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